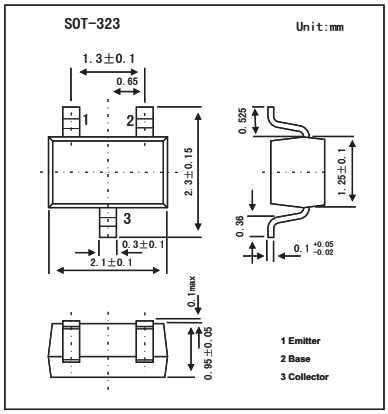
PNP High Voltage Amplifier
MMSTA92



Features

High breakdown voltage

Low collector-emitter saturation voltage

Complementary to MMSTA42

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current -Continuous	I_C	-300	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100 μA I_E=0	-300			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1 mA I_B=0	-300			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	I_E= 100 μA I_C=0	-5.0			V
Collector cutoff current	I_{CBO}	V_{CB}= -200 V , I_E=0			-0.25	μA
Collector cutoff current	I_{EBO}	V_{CE}= -3.0V , I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}= -10V, I_C= -1.0mA	60			
		V_{CE}= -10V, I_C= -10mA	100		200	
		V_{CE}= -10V, I_C= -30mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-20 mA, I_B= -2.0mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-20 mA, I_B= -2.0mA			-0.9	V
Transition frequency	f_T	V_{CE}= -20V, I_C= -10mA,f=100MHz	50			MHz
Output Capacitance	C_{ob}	V_{CB}=-20V,f=1.0MHz,I_E=0			6.0	pF

Marking

Marking	K3R